## NSN 5961-00-882-4153

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-882-4153 **Inclosure Material:** Metal and plastic **Overall Length:** 0.650 inches **Overall Height:** 0.169 inches **Overall Width:** 0.250 inches **Function For Which Designed:** Phototransistor **Mounting Facility Quantity: Mounting Method:** Threaded hole **Thread Size:** 0.060 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 collector-to-emitter voltage, instantaneous and 7.0 emitter to collector voltage, dc **Current Rating Per Characteristic:** 2.00 milliamperes collector cutoff current, dc, emitter open and 5.00 milliamperes peak forward surge current **Power Rating Per Characteristic:** 50.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 unthreaded hole Shelf Life: N/a **Unit Of Measure:** 

**Demilitarization:** 

Yes - demil/mli

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